

# 30V N-Channel Power MOSFET



**SOT-26** 

## 1. Dr. 2. Dr.

#### Pin Definition:

Drain
 Drain
 Drain
 Drain
 Source

#### Note:

MSL 1 (Moisture Sensitivity Level) per J-STD-020

## **Key Parameter Performance**

Parameter		Value	Unit	
$V_{DS}$		30	V	
R <sub>DS(on)</sub> (max)	V <sub>GS</sub> = 10V	24	mΩ	
	V <sub>GS</sub> = 4.5V	34		
$Q_g$		4.1	nC	

### **Features**

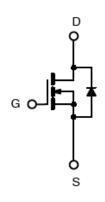
- Halogen-free
- Improved dV/dt capability
- Fast Switching

## **Ordering Information**

Ordering code	Package	Packing			
TSM240N03CX6 RFG	SOT-26	3kpcs / 7" Reel			

Note: Halogen-free according to IEC 61249-2-21 definition

## **Block Diagram**



N-Channel MOSFET

### **Absolute Maximum Ratings** (T<sub>C</sub> = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V <sub>DS</sub>	30	V
Gate-Source Voltage		V <sub>GS</sub>	±20	V
Continuous Drain Current	$T_C = 25^{\circ}C$	l <sub>D</sub>	6.5	Α
	T <sub>C</sub> = 100°C		4.1	Α
Pulsed Drain Current (Note 1)		I <sub>DM</sub>	26	Α
Single Pulse Avalanche Energy (Note 2)		E <sub>AS</sub>	32	mJ
Power Dissipation @ T <sub>C</sub> = 25°C		P <sub>D</sub>	1.56	W
Operating Junction Temperature		TJ	150	°C
Storage Temperature Range		T <sub>STG</sub>	-55 to +150	°C

### **Thermal Performance**

Parameter	Symbol	Limit	Unit	
Thermal Resistance - Junction to Ambient	$R_{\Theta JA}$	80	°C/W	

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**Electrical Specifications** (T<sub>C</sub> = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static				<u>I</u>		
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	30			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_{D} = 6A$	R <sub>DS(on)</sub>		17	24	mΩ
	$V_{GS} = 4.5V, I_D = 4A$			22	34	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V <sub>GS(TH)</sub>	1.2	1.4	2.5	V
	$V_{DS} = 30V, V_{GS} = 0V$				1	μА
Zero Gate Voltage Drain Current	V <sub>DS</sub> = 24V, T <sub>J</sub> = 125°C	I <sub>DSS</sub>			10	
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Forward Transconductance (Note 3)	$V_{DS} = 10V, I_{D} = 4A$	<b>g</b> fs		6.5		S
Dynamic	1				L	
Total Gate Charge (Note 3,4)		$Q_g$		4.1		nC
Gate-Source Charge (Note 3,4)	$V_{DS} = 15V, I_{D} = 6A,$	$Q_gs$		1		
Gate-Drain Charge (Note 3,4)	$V_{GS} = 4.5V$	$Q_gd$		2.1		
Input Capacitance		C <sub>iss</sub>		345		
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	C <sub>oss</sub>		55		pF
Reverse Transfer Capacitance		C <sub>rss</sub>		32		,
Switching					l .	
Turn-On Delay Time (Note 3,4)		t <sub>d(on)</sub>		2.8		
Turn-On Rise Time (Note 3,4)	$V_{DD} = 15V, I_D = 1A,$	t <sub>r</sub>		7.2		
Turn-Off Delay Time (Note 3,4)	$V_{GS} = 10V, R_{GEN} = 6\Omega$	t <sub>d(off)</sub>		15.8		ns
Turn-Off Fall Time (Note 3,4)		t <sub>f</sub>		4.6		
Source-Drain Diode Ratings and Ch	aracteristic				L	
Maximum Continuous Drain-Source	Integral reverse diode in the MOSFET	,			0.5	Δ.
Diode Forward Current		I <sub>S</sub>			6.5	Α
Maximum Pulse Drain-Source Diode		I <sub>SM</sub>			26	Α
Forward Current						
Diode-Source Forward Voltage	$V_{GS} = 0V$ , $I_S = 1A$	$V_{SD}$			1	V

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#### Note:

- 1. Pulse width limited by safe operating area
- 2. L = 1mH,  $I_{AS}$  = 8A,  $V_{DD}$  = 25V,  $R_G$  = 25 $\Omega$ , Starting  $T_J$  = 25 $^{\circ}$ C
- 3. Pulse test: pulse width  $\leq$  300 $\mu$ s, duty cycle  $\leq$  2%
- 4. Switching time is essentially independent of operating temperature.

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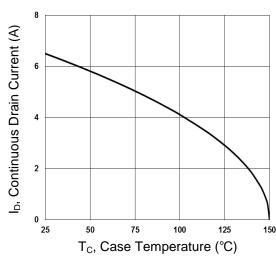


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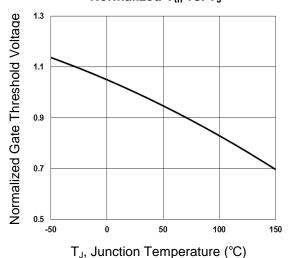


#### **Electrical Characteristics Curve**

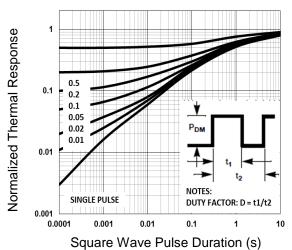




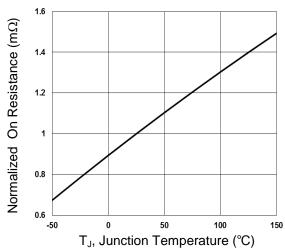
### Normalized $V_{th}$ vs. $T_J$



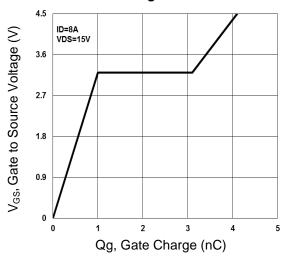
**Normalized Transient Impedance** 



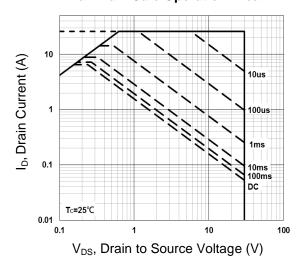
Normalized RDSON vs. T<sub>J</sub>



**Gate Charge Waveform** 



**Maximum Safe Operation Area** 



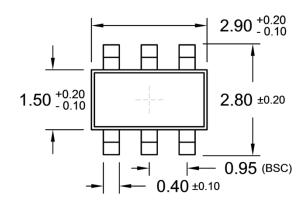
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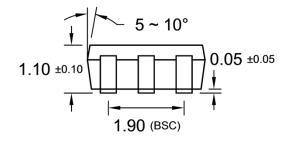


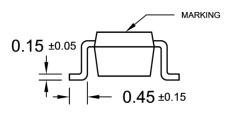
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# **SOT-26 Mechanical Drawing**

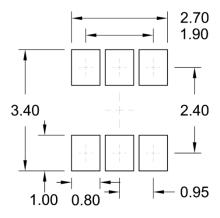






**Unit: Millimeters** 

## SUGGESTED PAD LAYOUT (Unit: Millimeters)



# **Marking Diagram**



24 = Device Code

Y = Year Code

M = Month Code for Halogen Free Product (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

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L = Lot Code

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# Pb RóHS

# TSM240N03CX6 30V N-Channel Power MOSFET

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